Product Preview

Unbuffered Inverter

MC74VHC1GU04

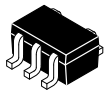
The MC74VHC1GU04 is an advanced high speed CMOS Unbuffered inverter fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

This device consists of a single unbuffered inverter. In combination with others, or in the MC74VHCU04 Hex Unbuffered Inverter, these devices are well suited for use as oscillators, pulse shapers, and in many other applications requiring a high–input impedance amplifier. For digital applications, the MC74VHC1G04 or the MC74VHC04 are recommended.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output.

The MC74VHC1GU04 input structure provides protection when voltages up to 7V are applied, regardless of the supply voltage. This allows the MC74VHC1GU04 to be used to interface 5V circuits to 3V circuits.

- High Speed: t_{PD} = 3.5ns (Typ) at V_{CC} = 5V
- Low Power Dissipation: I_{CC} = 2μA (Max) at T_A = 25°C
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300mA
- ESD Performance: HBM > 2000V; MM > 200V, CDM > 1500V
- Chip Complexity: 2 FETs or 1 Equivalent Gates



DF SUFFIX
5–LEAD SOT–353 PACKAGE
SC–88A
CASE 419A–01

FUNCTION TABLE

A Input	$\overline{Y}$ Output
L	H
H	L

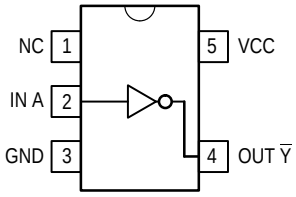


Figure 1. 5–Lead SOT–353 Pinout (Top View)

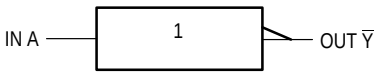
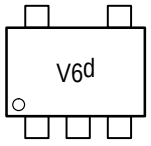


Figure 2. Logic Symbol



Pin 1
d = Date Code

Marking Diagram

DEVICE ORDERING INFORMATION

Device Order Number	Device Nomenclature						Package Type	Tape and Reel Size
	Motorola Circuit Indicator	Temp Range Identifier	Technology	Device Function	Package Suffix	Tape and Reel Suffix		
MC74VHC1GU04DFT1	MC	74	VHC1G	U04	DF	T1	SC–88A	7–Inch/3000 Unit

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MAXIMUM RATINGS*

Characteristics	Symbol	Value	Unit
DC Supply Voltage	V_{CC}	–0.5 to +7.0	V
DC Input Voltage	V_{IN}	–0.5 to +7.0	V
DC Output Voltage V_{CC} = 0 High or Low State	V_{OUT}	–0.5 to 7.0 –0.5 to V_{CC} + 0.5	V
Input Diode Current	I_{IK}	–20	mA
Output Diode Current (V_{OUT} < GND; V_{OUT} > V_{CC})	I_{OK}	+20	mA
DC Output Current, per Pin	I_{OUT}	+25	mA
DC Supply Current, V_{CC} and GND	I_{CC}	+50	mA
Power dissipation in still air, SC–88A †	P_D	200	mW
Lead temperature, 1 mm from case for 10 s	T_L	260	°C
Storage temperature	T_{stg}	–65 to +150	°C

* Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute–maximum–rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — SC–88A Package: –5 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Characteristics	Symbol	Min	Max	Unit
DC Supply Voltage	V_{CC}	2.0	5.5	V
DC Input Voltage	V_{IN}	0.0	5.5	V
DC Output Voltage	V_{OUT}	0.0	V_{CC}	V
Operating Temperature Range	T_A	–55	+125	°C
Input Rise and Fall Time V_{CC} = 3.3V ± 0.3V V_{CC} = 5.0V ± 0.5V	t_r , t_f	0 0	No Limit No Limit	ns/V

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} (V)	T_A = 25°C Min	T_A = 25°C Typ	T_A = 25°C Max	$T_A \leq$ 85°C Min	$T_A \leq$ 85°C Max	$T_A \leq$ 125°C Min	$T_A \leq$ 125°C Max	Unit
V_{IH}	Minimum High–Level Input Voltage		2.0 3.0 4.5 5.5		1.7 2.4 3.6 4.4			1.7 2.4 3.6 4.4		1.7 2.4 3.6 4.4	V
V_{IL}	Maximum Low–Level Input Voltage		2.0 3.0 4.5 5.5		0.3 0.6 0.9 1.1		0.3 0.6 0.9 1.1		0.3 0.6 0.9 1.1		V
V_{OH}	Minimum High–Level Output Voltage $V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = -50\mu A$	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		1.9 2.9 4.4		V
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = -4mA$ $I_{OH} = -8mA$	 3.0 4.5	 2.58 3.94			 2.48 3.80		 2.34 3.66		V
V_{OL}	Maximum Low–Level Output Voltage $V_{IN} = V_{IH}$ or V_{IL}	$V_{IN} = V_{IH}$ or V_{IL} $I_{OL} = 50\mu A$	2.0 3.0 4.5		0.0 0.0 0.0	0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OL} = 4mA$ $I_{OL} = 8mA$	 3.0 4.5			 0.36 0.36		 0.44 0.44		 0.52 0.52	V
I_{IN}	Maximum Input Leakage Current	$V_{IN} = 5.5V$ or GND	0 to 5.5			±0.1		±1.0		±1.0	µA
I_{CC}	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			2.0		20		40	µA

AC ELECTRICAL CHARACTERISTICS (C_{load} = 50 pF, Input $t_r = t_f$ = 3.0ns)

Symbol	Parameter	Test Conditions		T_A = 25°C Min	T_A = 25°C Typ	T_A = 25°C Max	$T_A \leq$ 85°C Min	$T_A \leq$ 85°C Max	$T_A \leq$ 125°C Min	$T_A \leq$ 125°C Max	Unit
t_{PLH}, t_{PHL}	Maximum Propogation Delay, Input A to $\overline{Y}$	$V_{CC} = 3.0 \pm 0.3V$	C_L = 15 pF C_L = 50 pF		5.0 7.5	8.9 11.4		10.5 13.0		12.0 15.5	ns
		$V_{CC} = 5.0 \pm 0.5V$	C_L = 15 pF C_L = 50 pF		3.5 5.0	5.5 7.0		6.5 8.0		8.0 9.5	
C_{IN}	Maximum Input Capacitance				4	10		10		10	pF

		Typical @ 25°C, V_{CC} = 5.0V	
C_{PD}	Power Dissipation Capacitance (Note 1.)	15	pF

1. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)} = C_{PD} \bullet V_{CC} \bullet f_{in} + I_{CC}$. C_{PD} is used to determine the no–load dynamic power consumption; $P_D = C_{PD} \bullet V_{CC}^2 \bullet f_{in} + I_{CC} \bullet V_{CC}$.

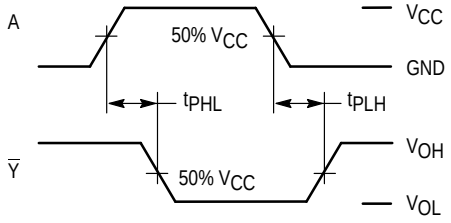
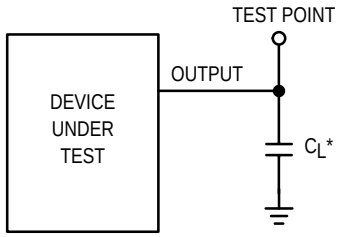


Figure 3. Switching Waveforms



* Includes all probe and jig capacitance

Figure 4. Test Circuit

OUTLINE DIMENSIONS

DF SUFFIX
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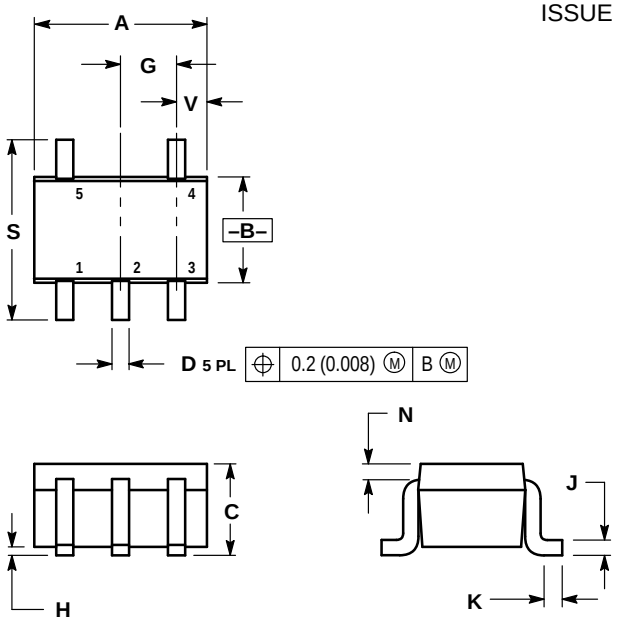
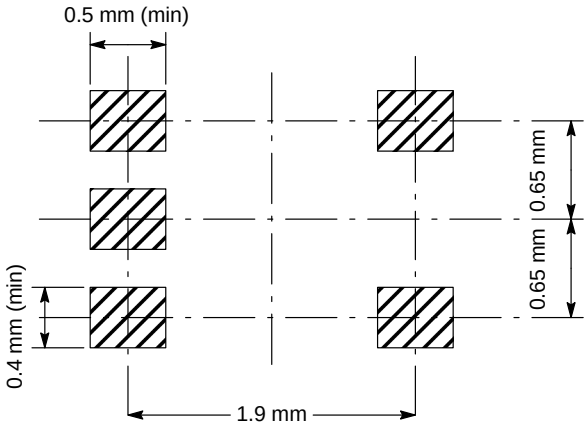
ISSUE B



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026 BSC		0.65 BSC	
H	—	0.004	—	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008 REF		0.20 REF	
S	0.079	0.087	2.00	2.20
V	0.012	0.016	0.30	0.40

SOT–353



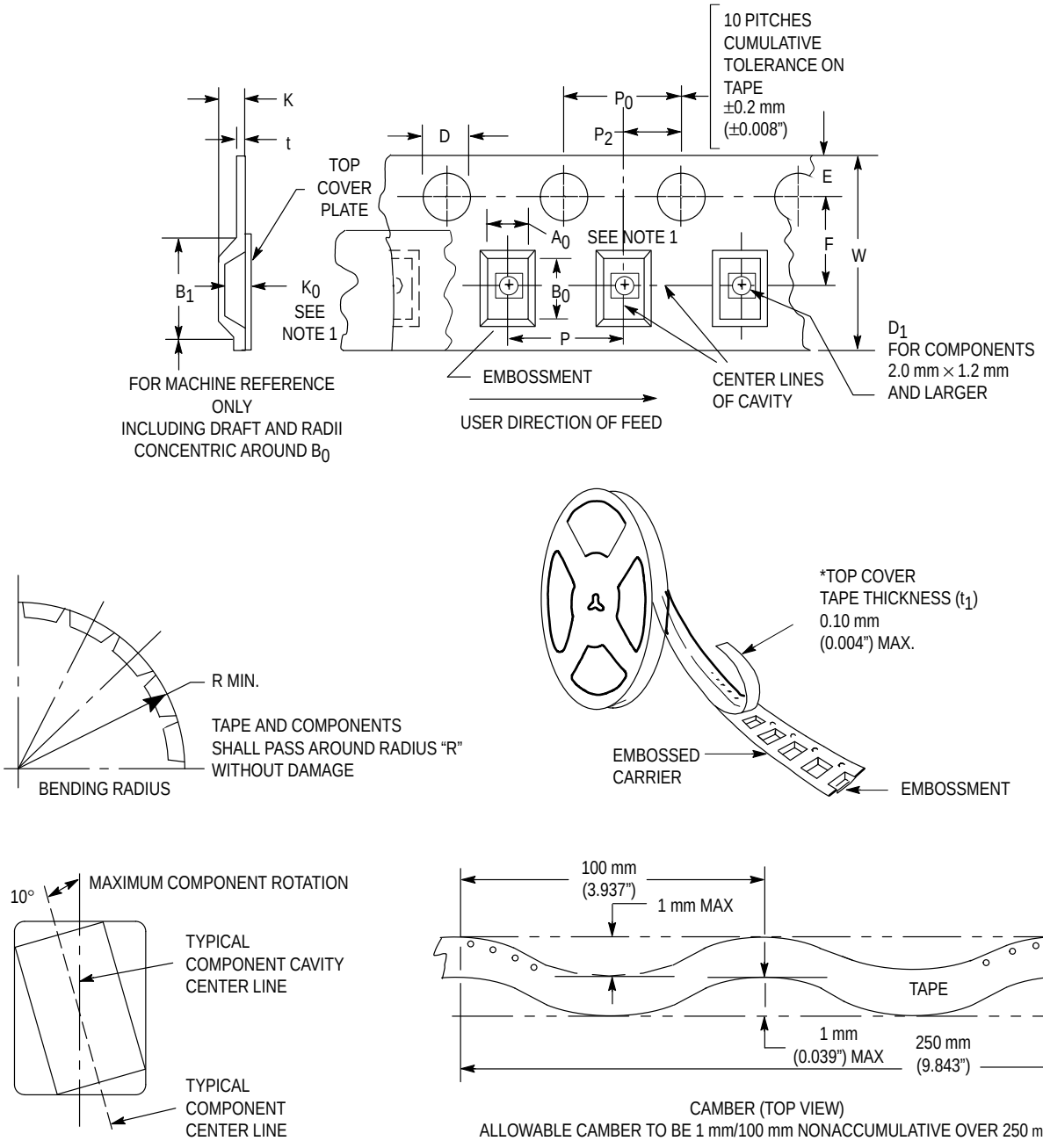


Figure 5. Carrier Tape Specifications

EMBOSSED CARRIER DIMENSIONS (See Notes 1 and 2)

Tape Size	B_1 Max	D	D_1	E	F	K	P	P_0	P_2	R	T	W
8 mm	4.55 mm (0.179")	1.5 +0.1/ –0.0 mm (0.059 +0.004/ –0.0")	1.0 mm Min (0.039")	1.75 ±0.1 mm (0.069 ±0.004")	3.5 ±0.5 mm (1.38 ±0.002")	2.4 mm (0.094")	4.0 ±0.10 mm (0.157 ±0.004")	4.0 ±0.1 mm (0.156 ±0.004")	2.0 ±0.1 mm (0.079 ±0.002")	25 mm (0.98")	0.3 ±0.05 mm (0.01 +0.0038/ –0.0002")	8.0 ±0.3 mm (0.315 ±0.012")

1. Metric Dimensions Govern–English are in parentheses for reference only.
2. A_0, B_0, and K_0 are determined by compnent size. The clearance between the components and the cavity must be within 0.05 mm min to 0.50 mm max. The component cannot rotate more than 10° within the determined cavity

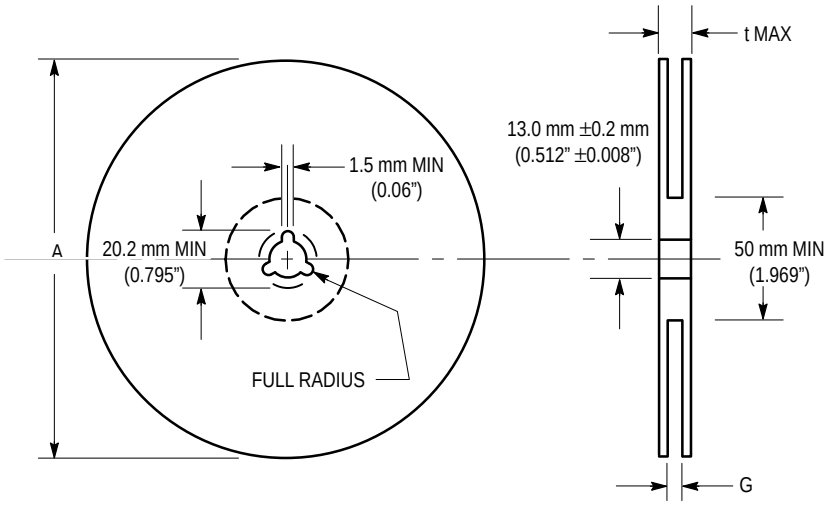


Figure 6. Reel Dimensions

REEL DIMIENSIONS

Tape Size	A Max	G	t Max
8 mm	330 mm (14.1")	8.400 mm, +1.5 mm, –0.0 (0.33", +0.059", –0.00)	14.4 mm (0.56")

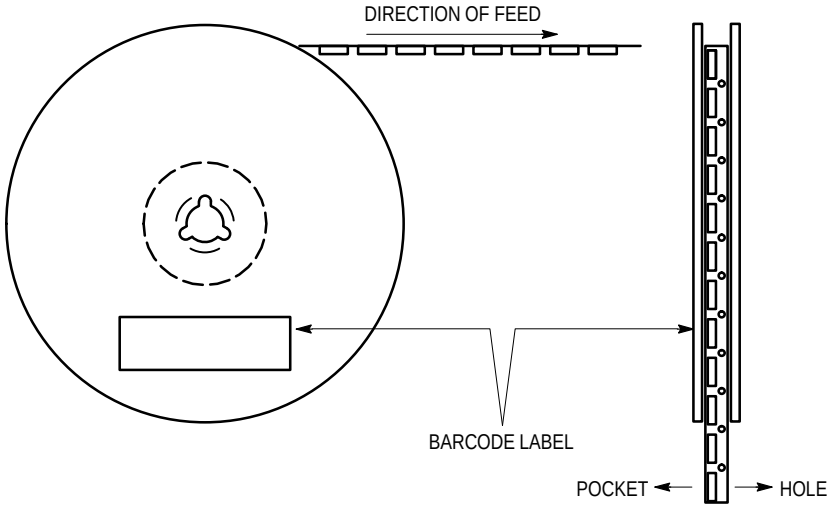


Figure 7. Reel Winding Direction

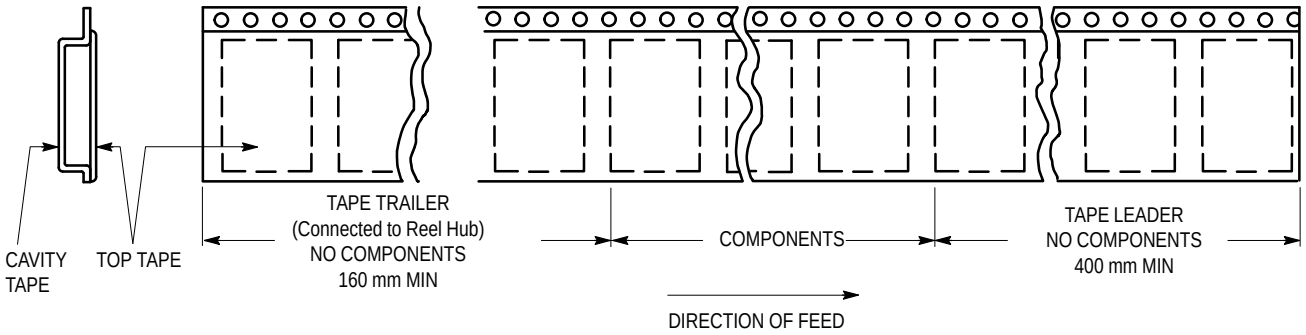


Figure 8. Tape Ends for Finished Goods

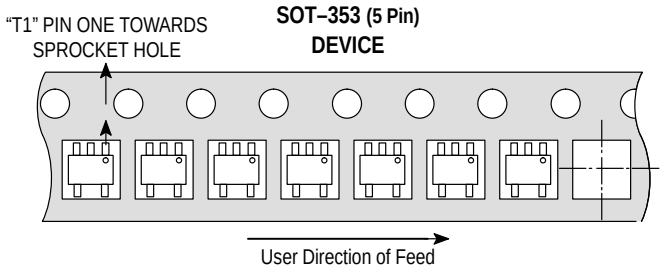


Figure 9. Reel Configuration

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